

AN3211K, AN3211S

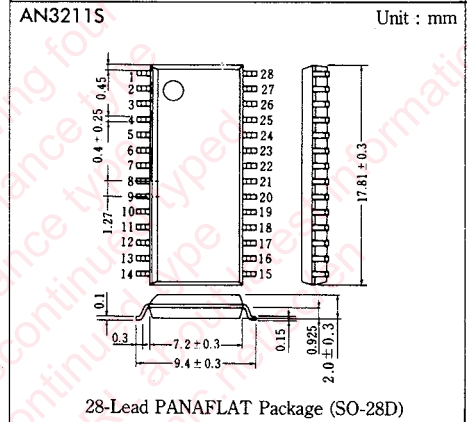
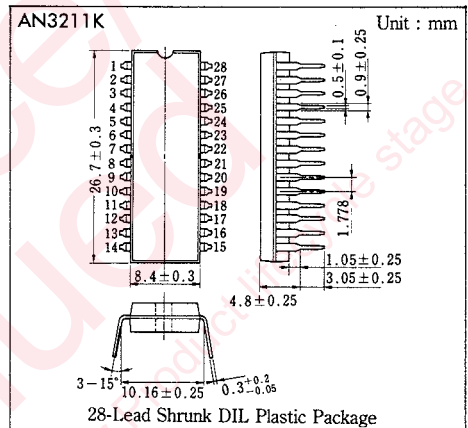
VTR Recording Video Signal Processing Circuits

Outline

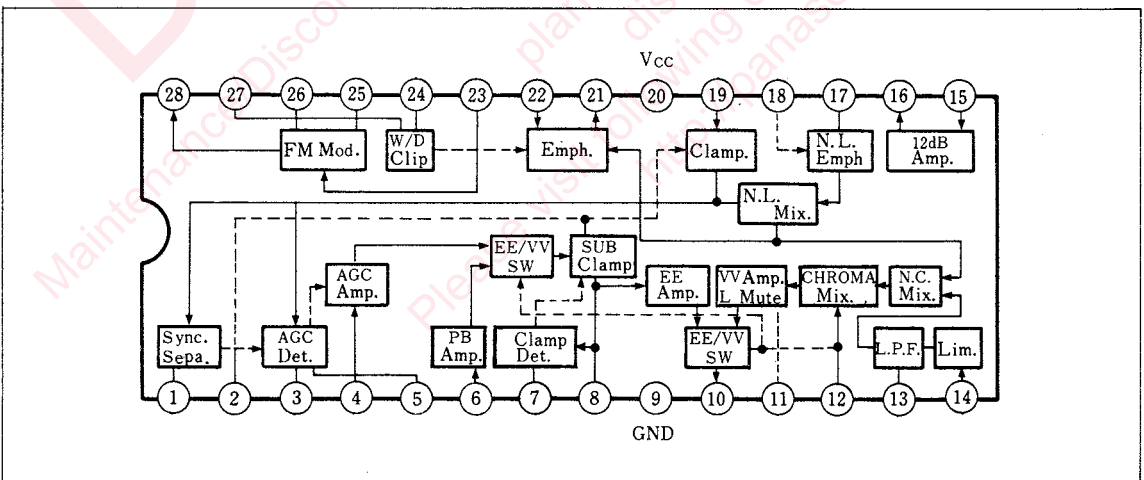
The AN3211K and the AN3211S are integrated circuits designed for VTR recording video signal processing circuits.

Features

- Dynamic emphasis characteristics : 5.5dB(at f=1MHz, input level=-20dB)
- Built-in carrier interleaving circuit)
- Built-in low pass filter (sync-separation circuit)
- Supply voltage: $V_{cc}=5V$



Block Diagram



■ Absolute Maximum Ratings (Ta=25°C)

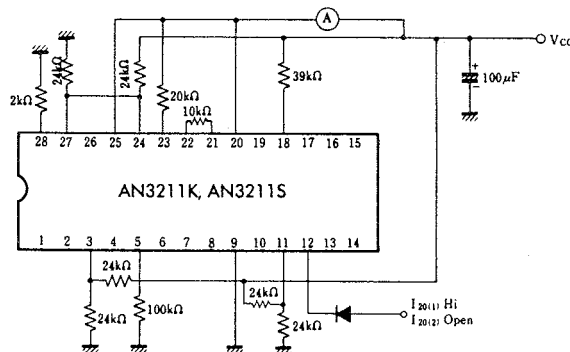
Item	Symbol	Rating	Unit
Supply Voltage	V _{CC}	6.0	V
Power Dissipation (Ta=70°C)	P _D	250	mW
Operating Ambient Temperature	T _{opr}	-20~+70	°C
Storage Temperature	T _{stg}	-55~+150	°C

■ Electrical Characteristics (V_{CC}=5V, Ta=25°C)

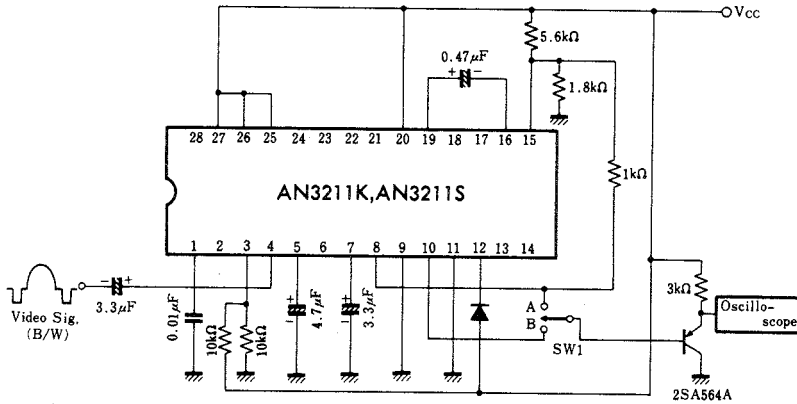
Item	Symbol	Test Circuit	Condition	min.	typ.	max.	Unit
Circuit Current(1)	I ₂₀₍₁₎	1	Pin ⑫ Hi (Rec.)	14.5		35.5	mA
Circuit Current(2)	I ₂₀₍₂₎	1	Pin ⑫ Open (PB)	14.5		35.5	mA
AGC Output Amplification	v ₈	2	Pin ⑫ Hi, Video Input 1V _{P-P}	0.4		0.8	V _{P-P}
AGC Control Sensitivity	Δv ₈	2	Pin ⑫ Hi, Video Input 0.5~2V _{P-P}			1.5	dB
PB Amp. Gain	G ₆₋₈	3	Pin ⑫ Open	6.8		9.9	dB
12dB Amp. Gain	G ₁₅₋₁₆	3		10.4		13.4	dB
FM Oscillation Frequency	f _o	4	Pin ⑫ Hi, Co=39pF, Ro=12kΩ	2.9		3.9	MHz
FM Output 2nd High Frequency	2f _o	4	Pin ⑫ Hi, Co=39pF, Ro=12kΩ			-33	dB
FM Oscillation Output Amplification	v ₂₈	4	Pin ⑫ Hi, Co=39pF, Ro=12kΩ	0.65		1.35	V _{P-P}
Frequency Control Sensitivity FM Oscillation	β ₂₈	4	Pin ⑫ Hi, Co=39pF, Ro=8.2~15kΩ	11.4		14.5	kHz/μA
Sync. Spea. Input Sensitivity	S ₁₉	5	Video Input V/S=5/2	0.45			V _{P-P}
Sync. Spea. Output Amplification	v ₂	5	Video Input V/S=5/2	4.3			V _{P-P}
NL Limiter Gain	v ₁₇₋₂₁	6	Pin ⑫ Hi	20		40	mV _{P-P}
NL Limiter Output Amplification(1)	v ₂₁₍₁₎	6	Pin ⑫ Hi	26		64	mV _{P-P}
NL Limiter Output Amplification(2)	v ₂₁₍₂₎	6	Pin ⑫ Hi, Pin ⑩ Lo	6		2.6	mV _{P-P}
NC Limiter Gain	v ₁₄₋₁₀	7	Pin ⑫ Open	30		70	mV _{P-P}
NC Limiter Output Amplification	v ₁₀	7	Pin ⑫ Open	65		125	mV _{P-P}
EE Amp. Gain	G ₈₋₁₀	2	Pin ⑫ Hi	9.7		11.6	dB
VV Amp. Gain	v ₁₉₋₁₀	3	Pin ⑫ Open	1.65		2.15	V _{P-P}
Chroma Amp. Gain	G ₁₂₋₁₀	7		5.3		8.8	dB
EE/VV Crosstalk	CT ₁₉₋₁₀	8	E≥4.0V			-40	dB
Mute Crosstalk	CT ₁₉₋₁₀	8	Pin ⑫ Lo, Pin ⑪ Hi			-40	dB
EE/VV Changeover Sensitivity	S ₁₂	8		4			V
FM Oscillation Carrier Interleave	Δf _o *	9	Pin ⑫ Hi	5.9		9.9	kHz
V offset	Δv ₁₉₋₁₀ *	3	Pin ⑫ Lo	30		110	mV

Note : Operating Supply Voltage Range V_{CC}=4.5~5.5V * It is design value but not a guaranteed value.

Test Circuit 1 (I₂₀₍₁₎, I₂₀₍₂₎)

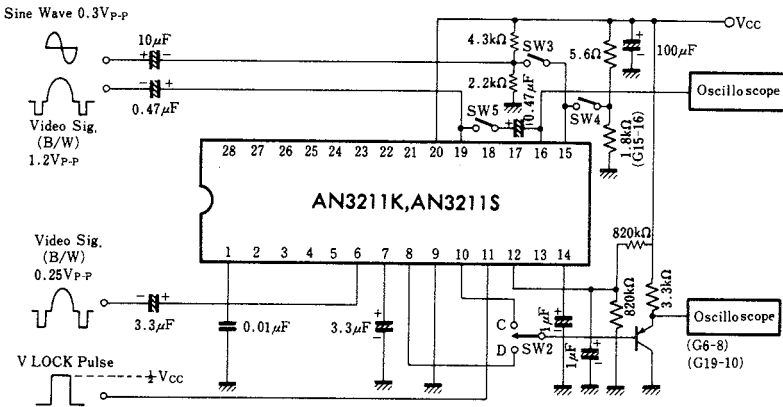


Test Circuit 2 (v_8 , Δv_8 , G_{8-10})



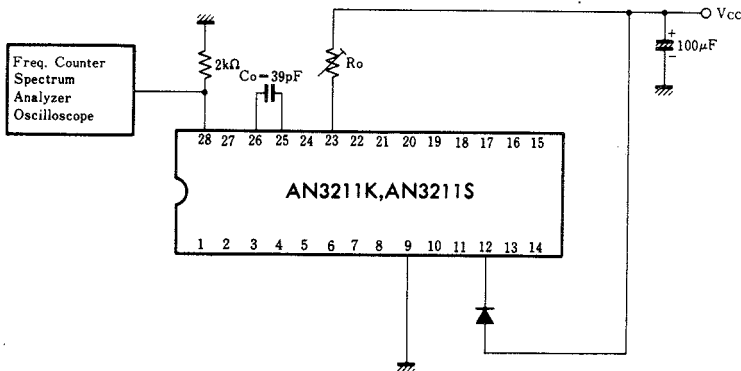
- v_8
IN: 1.0V_{P-P}
- Δv_8
Output amplification, change between IN: 0.5V_{P-P} to 2.0V_{P-P}
- G_{8-10}
IN: 1.0V_{P-P}
Ratio of output when SW1 is A to output when SW1 is B

Test Circuit 3 (G_{6-8} , G_{15-16} , v_{19-10} , Δv_{19-10})



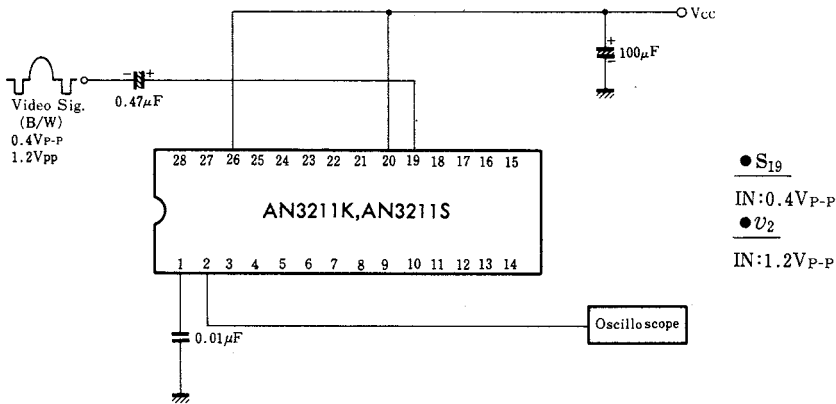
- G_{6-8}
IN: ⑥ pin 0.25V_{P-P}
SW2: D
- G_{15-16}
IN: ⑩ pin 0.3V_{P-P}
SW3: ON
SW4: OFF
SW5: OFF
- v_{19-10}
IN: ⑩ pin 1.2V_{P-P}
SW2: C
SW5: OFF
- Δv_{19-10}
IN: ⑩ pin 1.2V_{P-P}
SW2: C
SW5: OFF

Test Circuit 4 (f_0 , $2f_0$, v_{28} , β_{28})



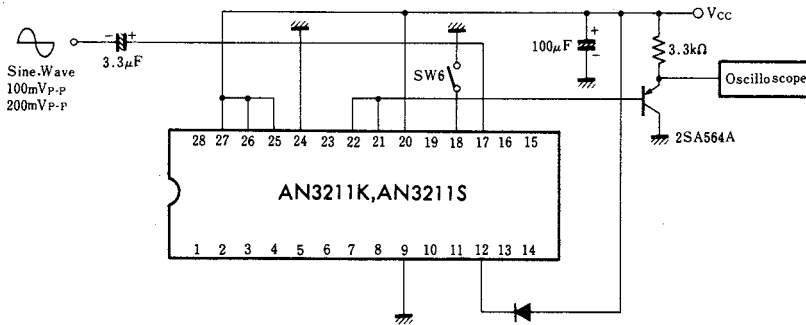
- $f_0, 2f_0, v_{28}$
 $R_o = 12k\Omega$
- β_{28}
Measure a change of oscillation frequency when $R_o = 8.2k\Omega \sim 15K\Omega$

Test Circuit 5 (S_{19} , v_2)



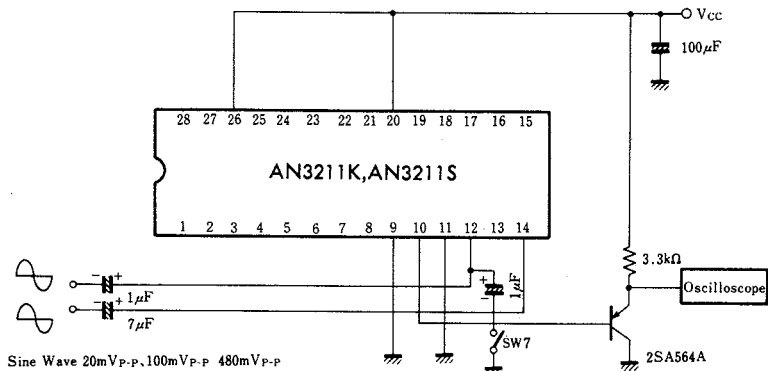
- S_{19}
IN: 0.4V_{P-P}
- v_2
IN: 1.2V_{P-P}

Test Circuit 6 (v_{17-21} , $v_{21(1)}$, $v_{21(2)}$)



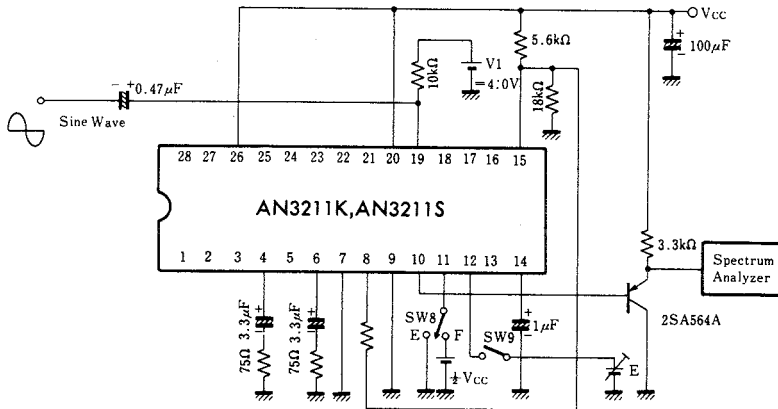
- v_{17-21}
IN: 100mV_{P-P}
- $v_{21(1)}$
IN: 200mV_{P-P}
SW6: OFF
- $v_{21(2)}$
IN: 200mV_{P-P}
SW6: ON

Test Circuit 7 (v_{14-10} , v_{10} , G_{12-10})



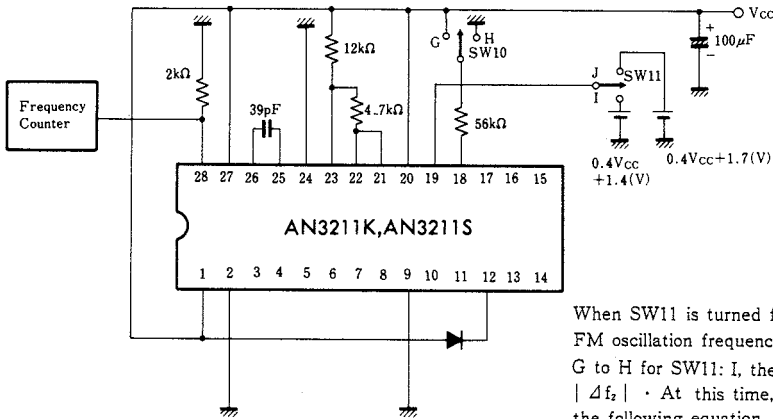
- v_{14-10}
IN: 20mV_{P-P}
1MHz
SW7: ON
- v_{10}
IN: 100mV_{P-P}
1MHz
SW7: ON
- G_{17-10}
IN: 480mV_{P-P}
1MHz
SW7: OFF

Test Circuit 8 (CT₁₉₋₁₀, CT'₁₉₋₁₀, S₁₂)



- CT₁₉₋₁₀
IN: 0.25V_{P-P} 1MHz
Measure the attenuation when SW8 is turned from OFF to ON.
- CT'₁₉₋₁₀
IN: 0.25V_{P-P} 1MHz
Measure the attenuation when SW8 is turned from E to F.
- S₁₂
IN: 0.25V_{P-P} 1MHz
Pin ② voltage when the output signal for SW9:ON becomes -40dB or less.

Test Circuit 9 (Δf₀)



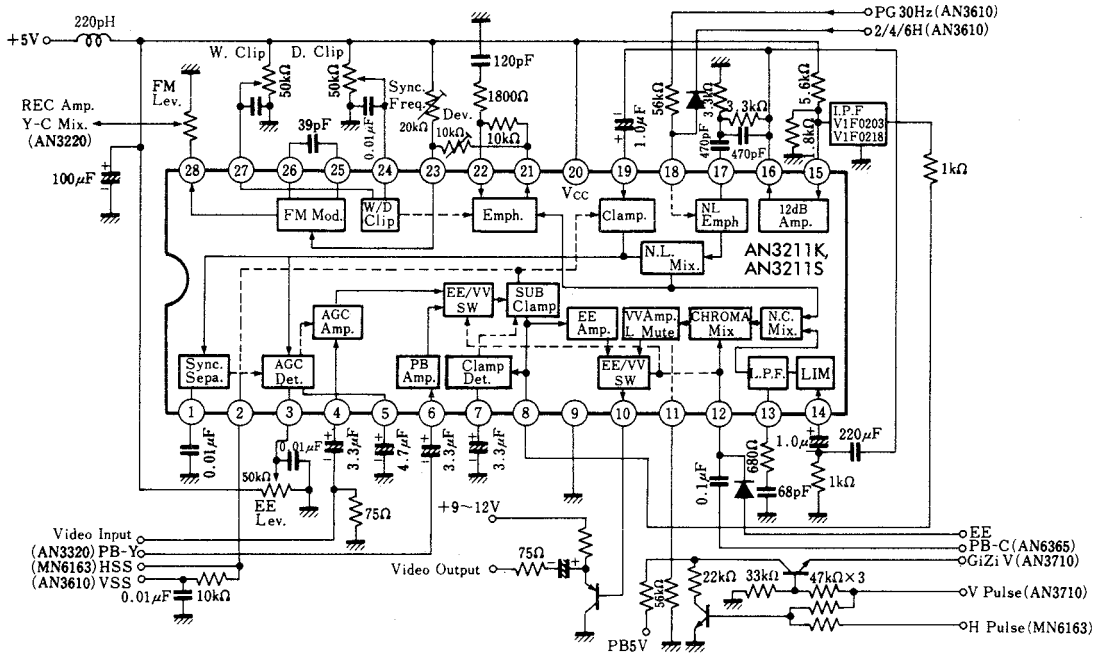
When SW11 is turned from I to J for SW10:G, the difference of FM oscillation frequency is $|\Delta f_1|$. When SW10 is turned from G to H for SW11: I, the difference of FM oscillation frequency is $|\Delta f_2|$. At this time, FM carrier interleave ratio Δf_0 is given by the following equation.

$$\Delta f_0 = \frac{|\Delta f_2|}{|\Delta f_1|} 250 \text{ (kHz)}$$

■ Pin

Pin No.	Pin Name	Pin No.	Pin Name
1	Sync Tip Level Detect	15	12dB Amp. Input
2	Sync Output	16	12dB Amp. Output
3	EE Level Adjustment	17	Non Linear Emphasis Sub-side Input
4	Video Signal Input During Recording	18	PG Input & 2/4/6H Select
5	AGC Detection	19	Main Clamp Input
6	Video Signal Input During PB	20	V _{cc}
7	Sub Clamp Detect	21	Main Emphasis Output
8	Sub Clamp Output	22	FB Amp. Input
9	GND	23	Mod. Input
10	EE/VV Output	24	Dark Clip Level Adjustment
11	Dummy Sync pulse Input	25	Mod.
12	PB Chroma Input	26	Mod.
13	Noise Canceller L.P.F.	27	White Clip Level Adjustment
14	Noise Canceller H.P.F.-side Input	28	FM Output

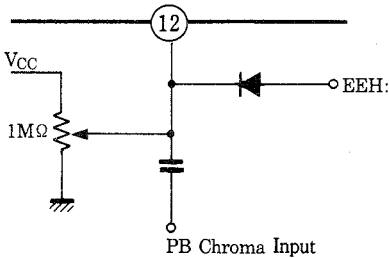
Application Circuit



Notes for Use

In the electrical characteristics table of dummy V offset V_{19-10} , -30 to 110 (mV) is listed as reference value. If exceeded beyond this max. value, V synchronization for special regeneration is not made, resulting in being under minimum of the value. In such cases, a skew may be generated on the top of the display screen. In these specifications for product, the reference value, from the view point of the set quality purpose, is listed just for reference for design. However, it is very unstable if used for ICs. So please be sure to take some measures such as external adjustment, etc. for this point when you use.

(Example of external adjustment circuit)



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